

IN THE CLAIMS:

Please amend claims 1-8 to read as follows:

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1. (Amended) A stacked semiconductor storage device comprising, in combination, a lower chip and an upper chip superimposed on a substrate, said semiconductor storage device further comprising:
a wiring substrate having wiring patterns thereon, interposed between said lower chip and said upper chip, for relaying electric connection between said upper chip and said substrate.
2. (Amended) A stacked semiconductor storage device as claimed in claim 1, wherein there are provided a first terminal connected to a terminal on a surface of said upper chip, a second terminal connected to a terminal on a surface of said substrate, and a wiring pattern for connecting said first and said second terminals on the surface of said wiring substrate.
3. (Amended) A stacked semiconductor storage device as claimed in claim 2, further comprising:
a first bonding wire for connecting said terminal of the surface of said upper chip with said first terminal; and
a second bonding wire for connecting said terminal of the surface of said substrate with said second terminal.
4. (Amended) A stacked semiconductor storage device as claimed in claim 1, wherein there is provided a wiring pattern whose one end is connected to a terminal on a rear surface of said upper chip, and whose other terminal is connected to a terminal on a surface of said lower chip.

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